

<b>Notice of References Cited</b>	Application/Control No. 10/812,947	Applicant(s)/Patent Under Reexamination YOSHIDA, SEIKOH	
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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	P	2002-198483	10-2001	Japan	Furukawa	H01L 029/778
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	W	Corlatan et al., Photoluminescence characterization of p-type GaN:Mg, Materials Research Society, 1998, pages 673-678.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.